



DOCUMENT CHANGE REQUEST

DCR number 517 Changes required for: General

Date: 2009/05/06

Date sent: 2009/05/06

Originator: S Jeffery - ESCC

Organisation: ESA/ESTEC

Status: IMPLEMENTED

Title: Transistors Silicon Switching PNP, based on type 2N3467

Number: 5208/009

Issue: 2

Other documents affected:

Page:

See attachment

Paragraph:

See attachment

Original wording:

Proposed wording:

Update the Maximum Ratings table (see the attachment for details) so that this detail spec is clear, complete and the content and format is in-line with other detail specifications for similar Part Types.

Justification:

Improve the content and clarity of the spec.

Attachments:

5208009_Issue_3_-_Draft_A.pdf, null

Modifications:

N/A

Approval signature:

Date signed:

2009-05-06



Pages 1 to 13

TRANSISTORS, SWITCHING, PNP

BASED ON TYPE 2N3467

ESCC Detail Specification No. 5208/009

as applicable

Issue 3 - Draft A	October 2008
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Document Custodian: European Space Agency - see <https://escies.org>



as applicable

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DOCUMENTATION CHANGE NOTICE

(Refer to <https://escies.org> for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
● 388	Specification up issued to incorporate editorial and technical changes per DCR.

t6d

At $T_{case} \leq +25^{\circ}C$

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	V_{CB0}	-40	V	Over entire operating temperature range
Collector-Emitter Voltage	V_{CEO}	-40	V	
Emitter-Base Voltage	V_{EBO}	-5	V	
Collector Current	I_C	-1	A	Continuous
Power Dissipation	P_{tot1}	1	W	At $T_{amb} \leq +25^{\circ}C$
	P_{tot2}	5	W	Note 1
Operating Temperature Range	T_{op}	-65 to +200	$^{\circ}C$	Note 1
Storage Temperature Range	T_{stg}	-65 to +200	$^{\circ}C$	Note 1
Soldering Temperature	T_{sol}	+265	$^{\circ}C$	Note 2

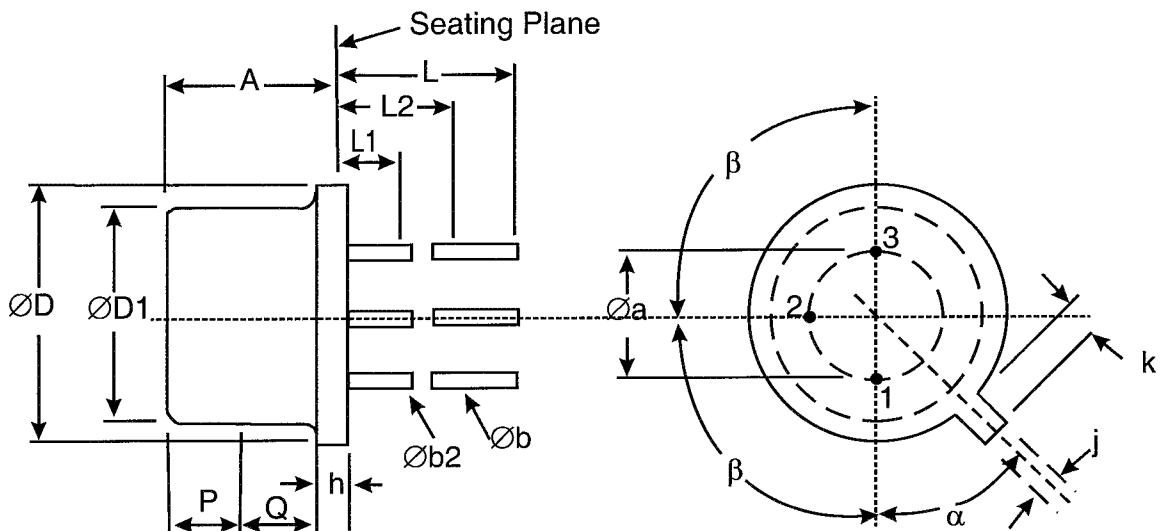
see attached

NOTES:

- For $T_{amb} > +25^{\circ}C$, derate linearly to 0W at $+200^{\circ}C$
- For Variants with tin-lead plating or hot solder dip lead finish all testing performed at $T_{amb} > +125^{\circ}C$ shall be carried out in a 100% inert atmosphere.
- Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

1.6 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.6.1 Metal Can Package (TO-39) - 3 lead



Symbols	Dimensions mm		Notes
	Min	Max	
$\varnothing a$	4.83	5.35	
A	6	6.6	
$\varnothing b$	0.4	0.533	2, 3
$\varnothing b2$	0.4	0.483	2, 3

Thermal Resistance, Junction-to-Ambient	$R_{th(j-a)}$	175	$^{\circ}\text{C}/\text{W}$	
Thermal Resistance, Junction-to-Case	$R_{th(j-c)}$	30	$^{\circ}\text{C}/\text{W}$	